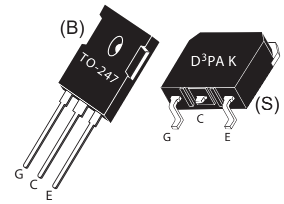
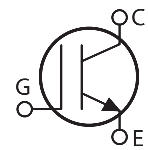
APT75GN60B(G)
APT75GN60S(G)
600V



Utilizing the latest Field Stop and Trench Gate technologies, these IGBT's have ultra low $V_{CE(ON)}$ and are ideal for low frequency applications that require absolute minimum conduction loss. Easy paralleling is a result of very tight parameter distribution and a slightly positive $V_{CE(ON)}$ temperature coefficient. A built-in gate resistor ensures extremely reliable operation, even in the event of a short circuit fault. Low gate charge simplifies gate drive design and minimizes losses.



- **600V Field Stop**
- **Trench Gate: Low $V_{CE(on)}$**
- **Easy Paralleling**
- **6µs Short Circuit Capability**
- **Intergrated Gate Resistor: Low EMI, High Reliability**

Applications: Welding, Inductive Heating, Solar Inverters, SMPS, Motor drives, UPS

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT75GN60B_S(G)	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current ⑧ @ T_C = 25°C	155	Amps
I_{C2}	Continuous Collector Current @ T_C = 110°C	93	
I_{CM}	Pulsed Collector Current ①	225	
SSOA	Switching Safe Operating Area @ T_J = 175°C	225A @ 600V	
P_D	Total Power Dissipation	536	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 175	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 4mA)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 1mA, T_j = 25°C)	5.0	5.8	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 75A, T_j = 25°C)	1.05	1.45	1.85	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 75A, T_j = 125°C)		1.87		
I_{CES}	Collector Cut-off Current (V_{CE} = 600V, V_{GE} = 0V, T_j = 25°C) ②			25	µA
	Collector Cut-off Current (V_{CE} = 600V, V_{GE} = 0V, T_j = 125°C) ②				
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			600	nA
$R_{G(int)}$	Intergrated Gate Resistor		4		Ω

These Devices are Sensitive to Electrostatic Discharge Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	**Capacitance** V_{GE} = 0V, V_{CE} = 25V f = 1 MHz		4500		pF
C_{oes}	Output Capacitance			370		
C_{res}	Reverse Transfer Capacitance			150		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge V_{GE} = 15V V_{CE} = 300V I_C = 75A		9.5		V
Q_g	Total Gate Charge ③			485		nC
Q_{ge}	Gate-Emitter Charge			30		
Q_{gc}	Gate-Collector ("Miller") Charge			270		
SSOA	Switching Safe Operating Area	T_J = 175°C, R_G = 4.3Ω⑦, V_{GE} = 15V, L = 100μH, V_{CE} = 600V	225			A
SCSOA	Short Circuit Safe Operating Area	V_{CC} = 600V, V_{GE} = 15V, T_J = 125°C, R_G = 4.3Ω⑦	6			μs
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (25°C)** V_{CC} = 400V V_{GE} = 15V I_C = 75A R_G = 1.0Ω⑦ T_J = +25°C		47		ns
t_r	Current Rise Time			48		
$t_{d(off)}$	Turn-off Delay Time			385		
t_f	Current Fall Time			38		
E_{on1}	Turn-on Switching Energy ④			2500		μJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤			3725		
E_{off}	Turn-off Switching Energy ⑥			2140		
$t_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{CC} = 400V V_{GE} = 15V I_C = 75A R_G = 1.0Ω⑦ T_J = +125°C		47		ns
t_r	Current Rise Time			48		
$t_{d(off)}$	Turn-off Delay Time			430		
t_f	Current Fall Time			55		
E_{on1}	Turn-on Switching Energy ④			2600		μJ
E_{on2}	Turn-on Switching Energy (Diode) ⑤			4525		
E_{off}	Turn-off Switching Energy ⑥			2585		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case **(IGBT)**			.28	°C/W
$R_{\theta JC}$	Junction to Case **(DIODE)**			N/A	
W_T	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance, not including $R_{G(int)}$ nor gate driver impedance. (MIC4452)

⑧ Continuous current limited by package pin temperature to 100A.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

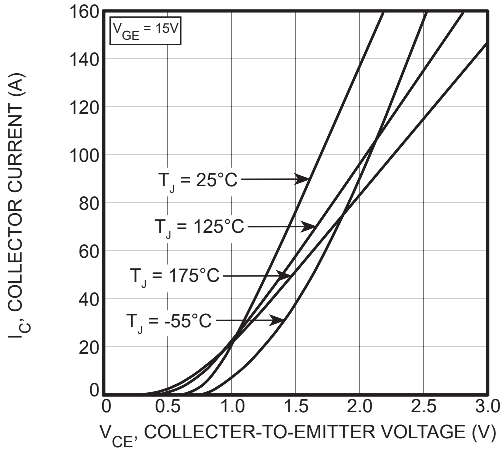


FIGURE 1, Output Characteristics(T_J = 25°C)

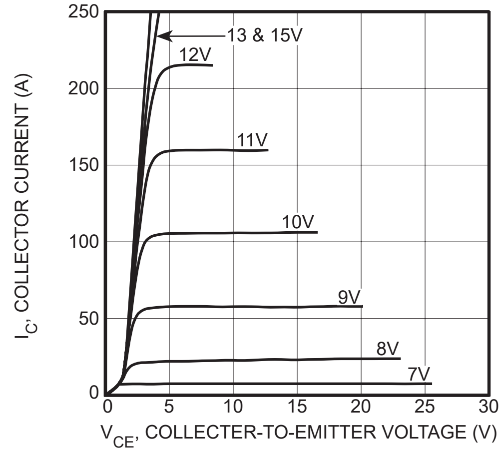


FIGURE 2, Output Characteristics (T_J = 125°C)

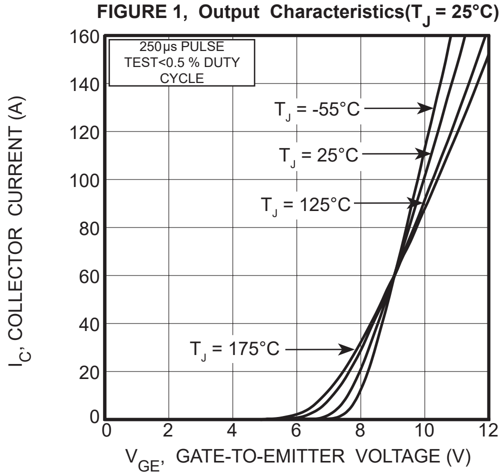


FIGURE 3, Transfer Characteristics

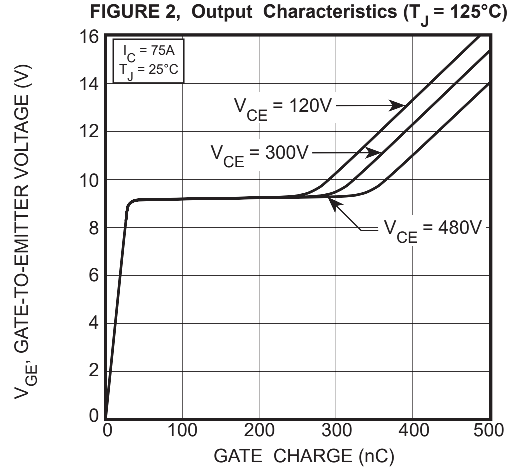


FIGURE 4, Gate Charge

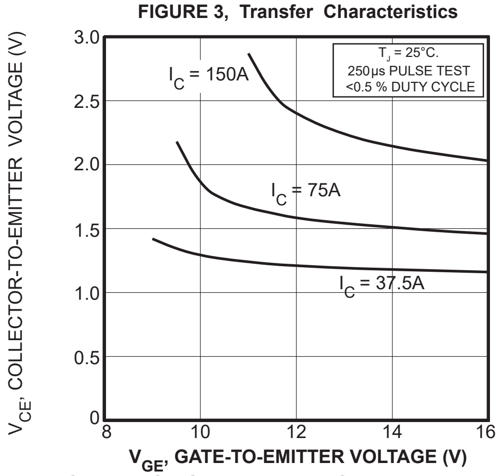


FIGURE 5, On State Voltage vs Gate-to- Emitter Voltage

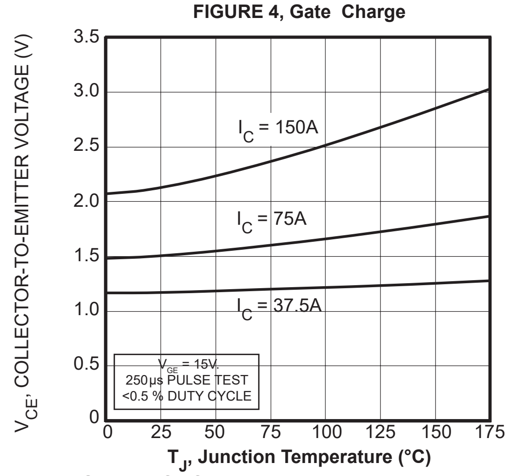


FIGURE 6, On State Voltage vs Junction Temperature

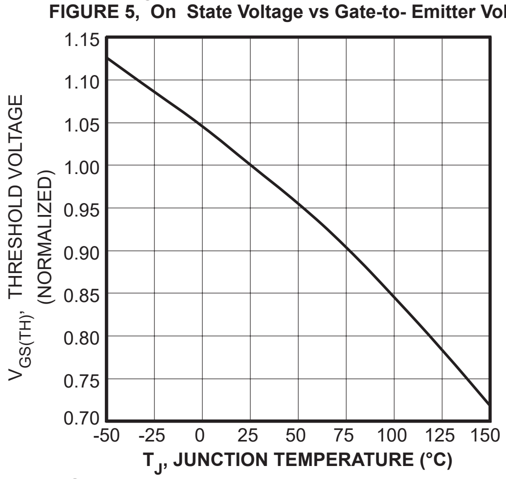


FIGURE 7, Threshold Voltage vs. Junction Temperature

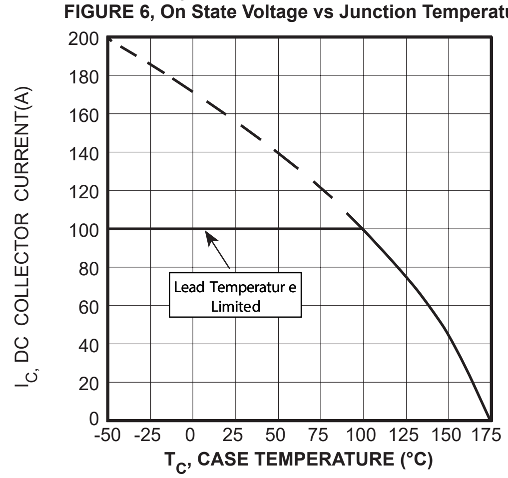


FIGURE 8, DC Collector Current vs Case Temperature

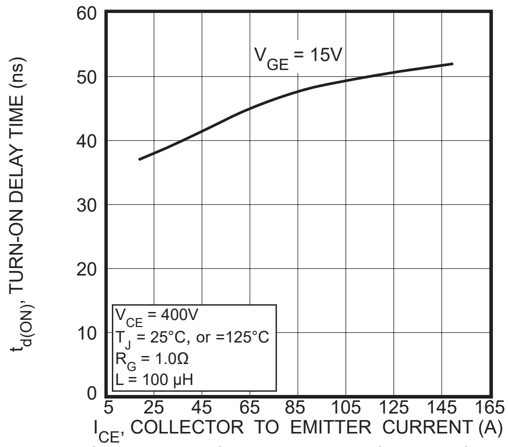


FIGURE 9, Turn-On Delay Time vs Collector Current

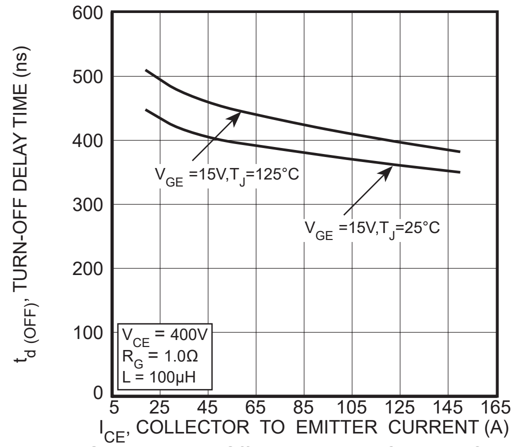


FIGURE 10, Turn-Off Delay Time vs Collector Current

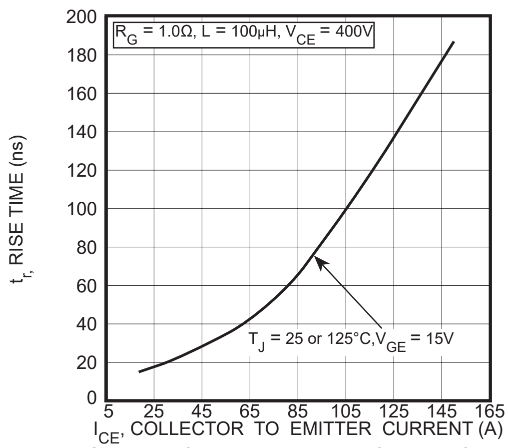


FIGURE 11, Current Rise Time vs Collector Current

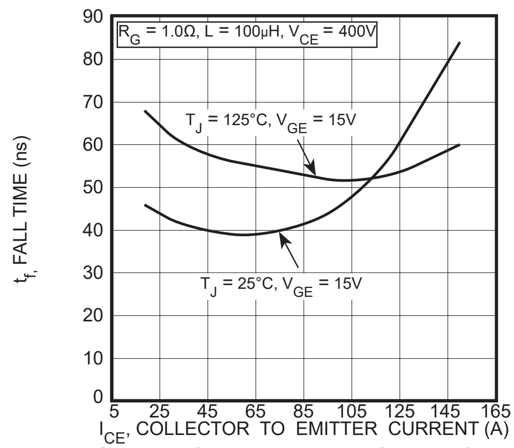


FIGURE 12, Current Fall Time vs Collector Current

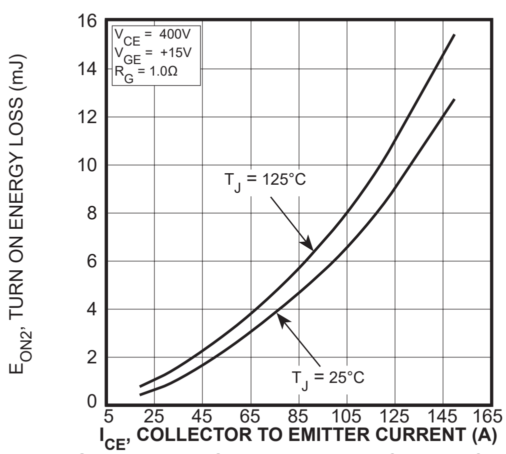


FIGURE 13, Turn-On Energy Loss vs Collector Current

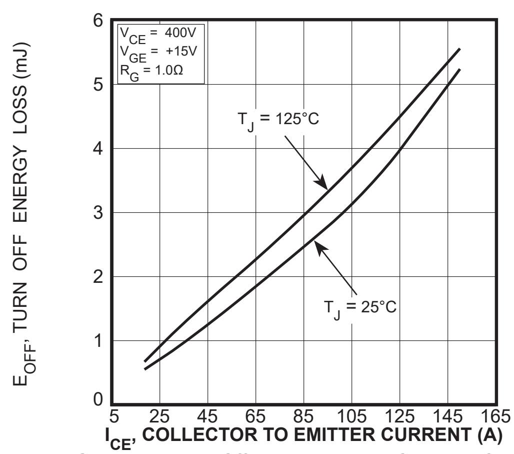


FIGURE 14, Turn Off Energy Loss vs Collector Current

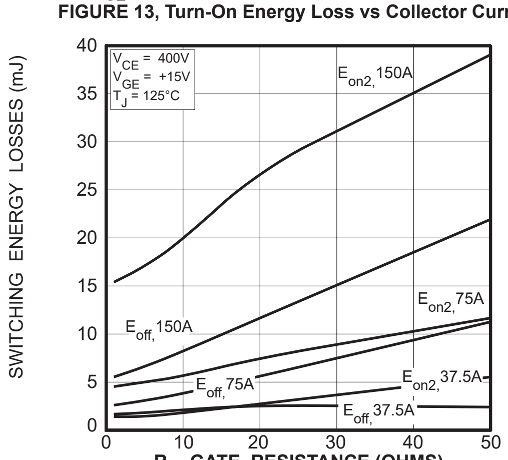


FIGURE 15, Switching Energy Losses vs. Gate Resistance

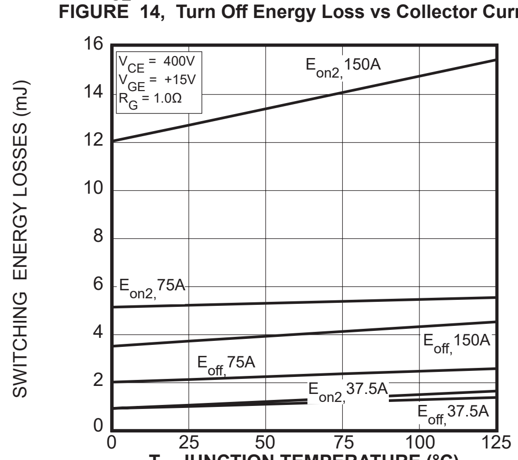


FIGURE 16, Switching Energy Losses vs Junction Temperature

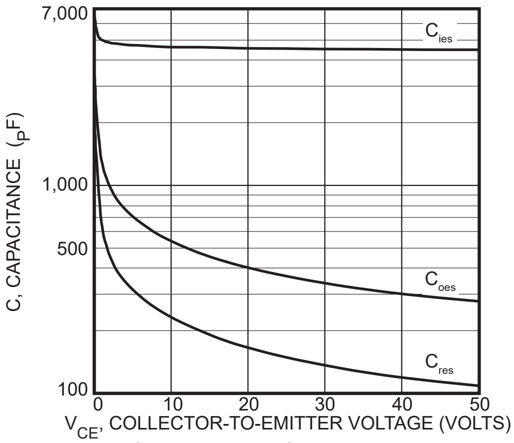


Figure 17, Capacitance vs Collector-To-Emitter Voltage

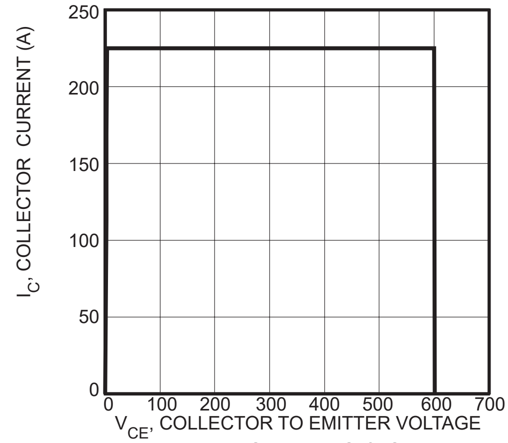


Figure 18,Minimum Switching Safe Operating Area

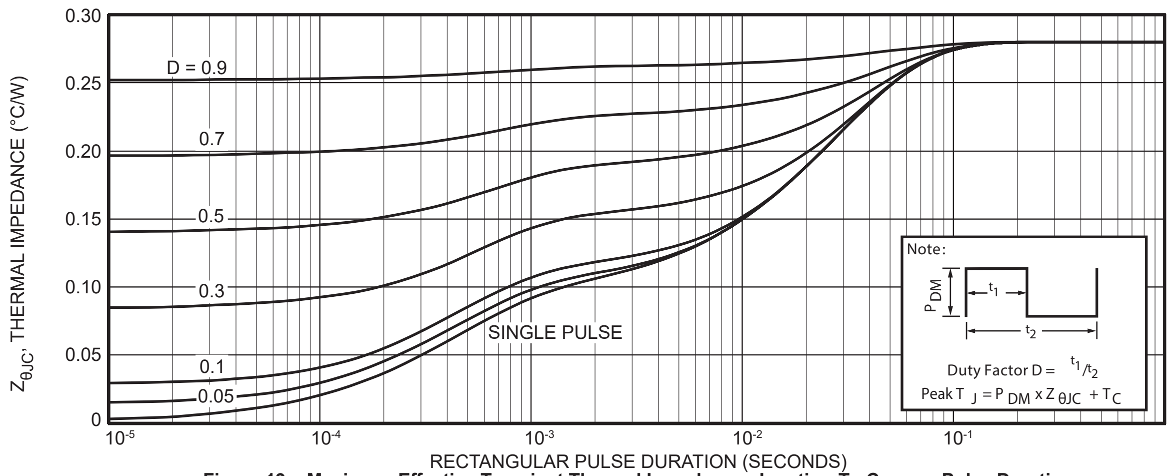


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

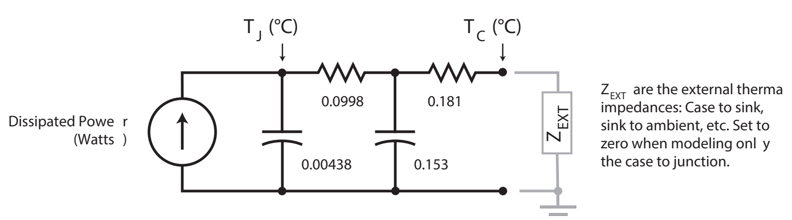
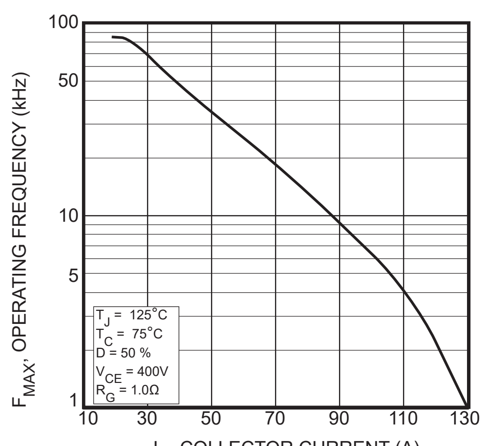


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL



$$F_{max} = \min(f_{max}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$

Figure 20, Operating Frequency vs Collector Current

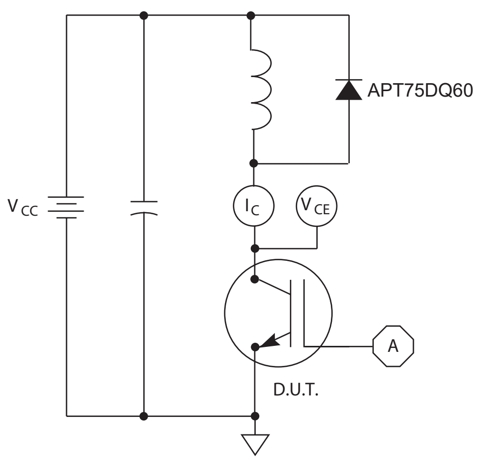


Figure 21, Inductive Switching Test Circuit

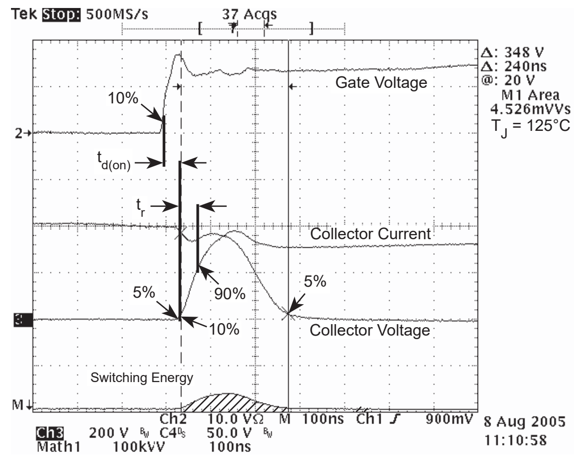


Figure 22, Turn-on Switching Waveforms and Definitions

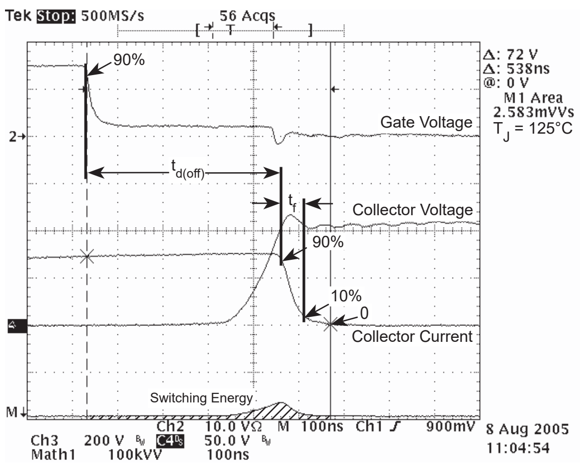
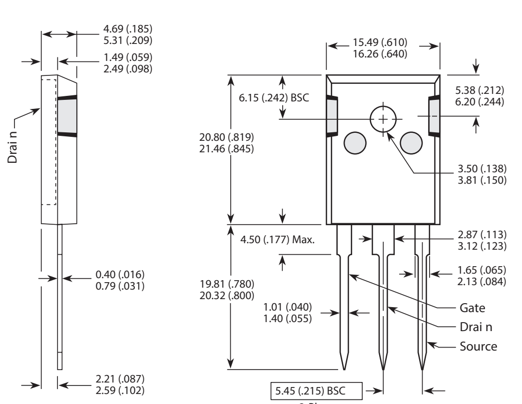
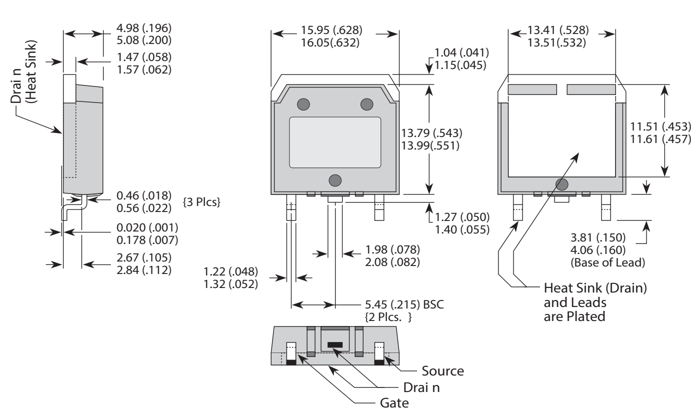


Figure 23, Turn-off Switching Waveforms and Definitions

TO-247 (B) Package Outline



D^3PAK (S) Package Outline



Dimensions in Millimeters (Inches)

Microsemi Power Matters.™

Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo, CA 92656 USA
Within the USA: +1 (800) 713-4113
Outside the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996
email: sales.support@microsemi.com
www.microsemi.com